

STM8301

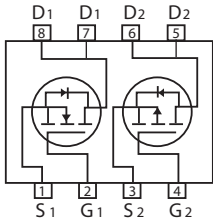
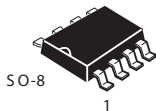
SamHop Microelectronics Corp.

Apr.28 2005 ver1.1

Dual Enhancement Mode Field Effect Transistor (N and P Channel)

PRODUCT (N-Channel)		
V _{DSS}	I _D	R _{DS(ON)} (m Ω) Max
30V	7A	25 @ V _{GS} = 10V
		42 @ V _{GS} = 4.5V

PRODUCT SUMMARY (P-Channel)		
V _{DSS}	I _D	R _{DS(ON)} (m Ω) Max
-30V	-4.5A	60 @ V _{GS} = -10V
		80 @ V _{GS} = -4.5V



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V _{DS}	30	-30	V
Gate-Source Voltage		V _{GS}	±20	±20	V
Drain Current-Continuous ^a @ T _a	25°C	I _D	7	-4.5	A
	70°C		6	-3.8	A
-Pulsed ^b		I _{DM}	29	-18	A
Drain-Source Diode Forward Current ^a		I _S	1.7	-1.7	A
Maximum Power Dissipation ^a	T _a = 25°C	P _D	2		W
	T _a =70°C		1.44		
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150		°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R θ JA	62.5	°C/W
--	---------------	------	------

STM8301

N-Channel ELECTRICAL CHARACTERISTICS (TA = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250uA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
ON CHARACTERISTICS ^b						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250uA	1	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 7A		20	25	m ohm
		V _{GS} = 4.5V, I _D = 5A		34	42	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	29			A
Forward Transconductance	g _{FS}	V _{DS} = 10V, I _D = 7A		10		S
DYNAMIC CHARACTERISTICS ^c						
Input Capacitance	C _{ISS}	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz		792		pF
Output Capacitance	C _{OSS}			133		pF
Reverse Transfer Capacitance	C _{RSS}			87		pF
SWITCHING CHARACTERISTICS ^c						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 15V I _D = 1A V _{GS} = 10V R _{GEN} = 6 ohm		6.5		ns
Rise Time	t _r			12.9		ns
Turn-Off Delay Time	t _{D(OFF)}			17.9		ns
Fall Time	t _f			5.2		ns
Total Gate Charge	Q _g	V _{DS} = 15V, I _D = 7A, V _{GS} = 10V		13.6		nC
		V _{DS} = 15V, I _D = 7A, V _{GS} = 4.5V		6.8		nC
Gate-Source Charge	Q _{gs}	V _{DS} = 15V, I _D = 7A, V _{GS} = 10V		2.0		nC
Gate-Drain Charge	Q _{gd}			3.5		nC

STM8301

P-Channel ELECTRICAL CHARACTERISTICS (TA=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V			-1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS ^b						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = -250uA	-1	-1.5	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D = -4.5A		50	60	m ohm
		V _{GS} =-4.5V, I _D = -3A		70	80	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} = -10V, V _{GS} = -10V	-18			A
Forward Transconductance	g _{FS}	V _{DS} = -10V, I _D = - 4.5A		9		S
DYNAMIC CHARACTERISTICS ^c						
Input Capacitance	C _{ISS}	V _{DS} =-15V, V _{GS} = 0V f =1.0MHz		586		pF
Output Capacitance	C _{OSS}			122		pF
Reverse Transfer Capacitance	C _{RSS}			78		pF
SWITCHING CHARACTERISTICS ^c						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = -15V I _D = -1A V _{GEN} = -10V R _{GEN} = 6 ohm		5.6		ns
Rise Time	t _r			4.7		ns
Turn-Off Delay Time	t _{D(OFF)}			51.8		ns
Fall Time	t _f			33.5		ns
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-4.5A, V _{GS} =-10V		11.2		nC
		V _{DS} =-15V, I _D =-4.5A, V _{GS} =-4.5V		5.4		nC
Gate-Source Charge	Q _{gs}	V _{DS} =-15V, I _D = - 4.5A, V _{GS} =-10V		1.4		nC
Gate-Drain Charge	Q _{gd}			2.7		nC

STM8301

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 1.7A	N-Ch	0.79	1.2	V
		V _{GS} = 0V, I _S = -1.7A	P-Ch	-0.8	-1.2	

Notes

a.Surface Mounted on FR4 Board, t ≤ 10sec.

* R_{θJA} is 62.5°C/W when mounted on 1in² FR-4 board with 2oz Copper

* R_{θJA} is 125°C/W when mounted on 0.02 in² FR-4 board with 2oz Copper

b.Pulse Test:Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

c.Guaranteed by design, not subject to production testing.

N-Channel

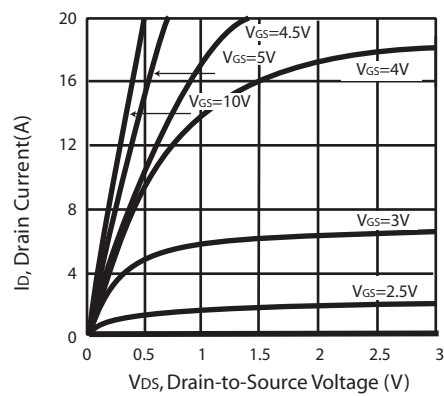


Figure 1. Output Characteristics

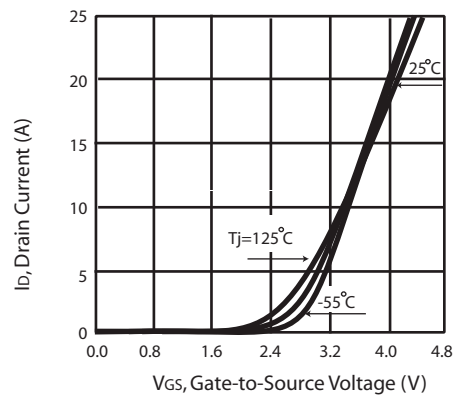


Figure 2. Transfer Characteristics

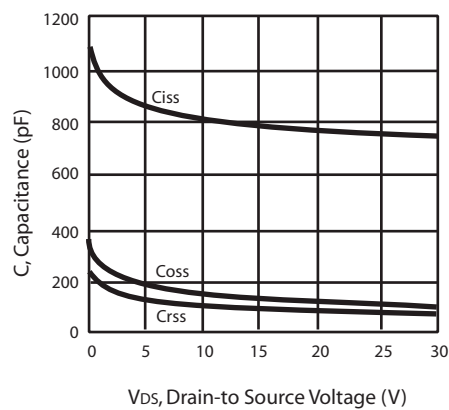


Figure 3. Capacitance

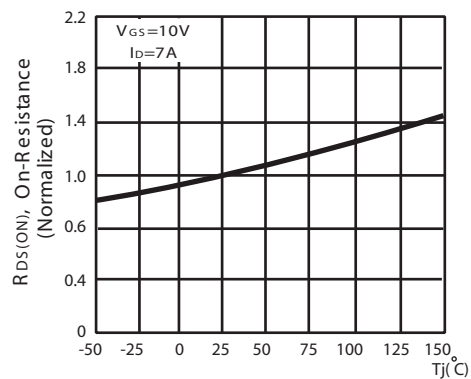


Figure 4. On-Resistance Variation with Drain Current and Temperature

STM8301

N-Channel

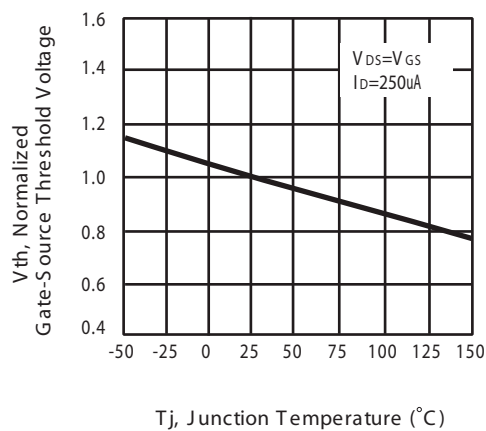


Figure 5. Gate Threshold Variation with Temperature

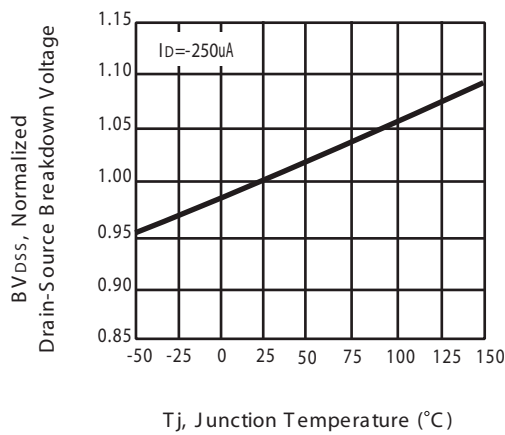


Figure 6. Breakdown Voltage Variation with Temperature

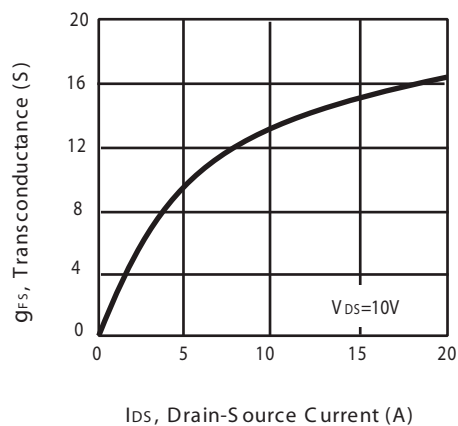


Figure 7. Transconductance Variation with Drain Current

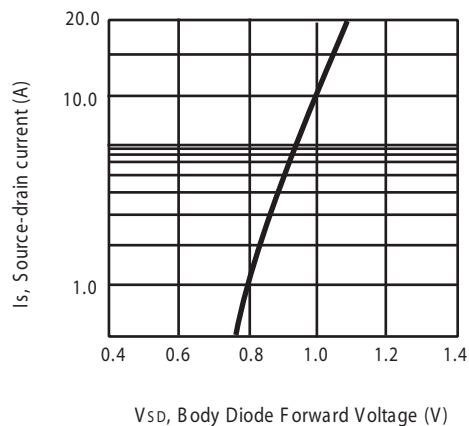


Figure 8. Body Diode Forward Voltage Variation with Source Current

STM8301

P-Channel

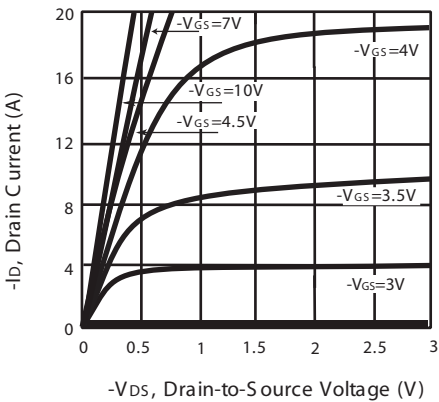


Figure 1. Output Characteristics

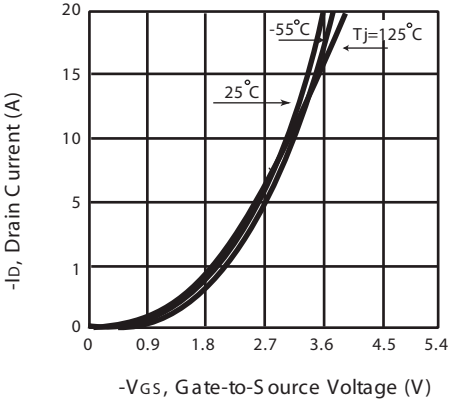


Figure 2. Transfer Characteristics

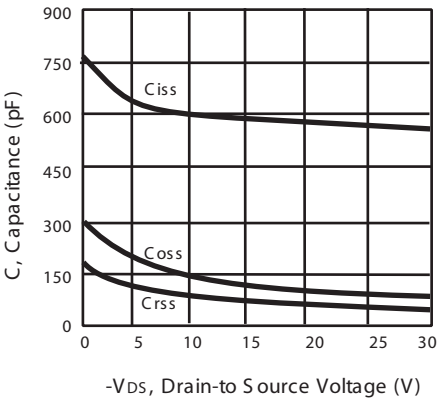


Figure 3. Capacitance

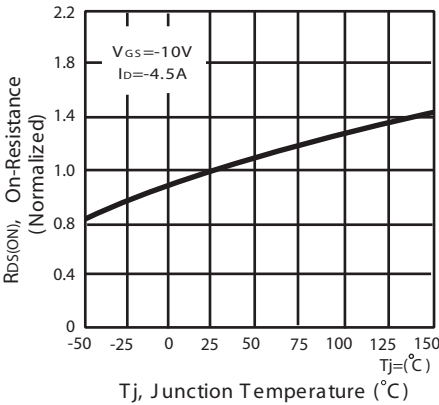


Figure 4. On-Resistance Variation with Temperature

STM8301

P-Channel

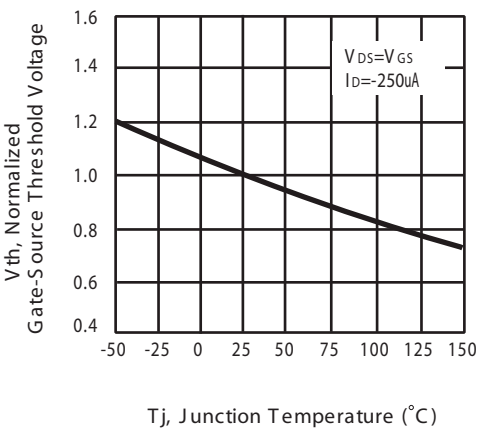


Figure 5. Gate Threshold Variation with Temperature

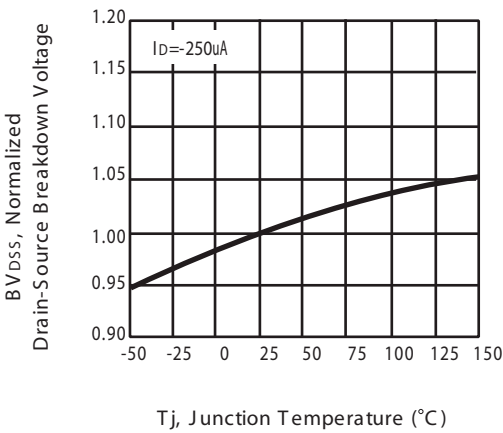


Figure 6. Breakdown Voltage Variation with Temperature

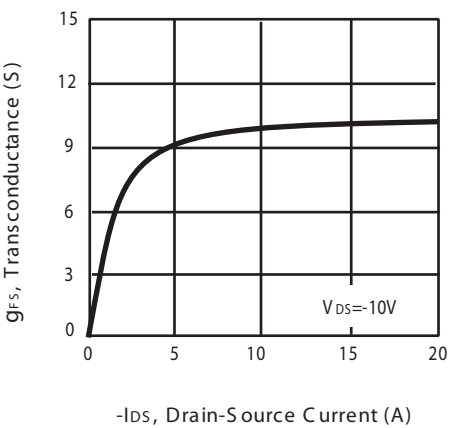


Figure 7. Transconductance Variation with Drain Current

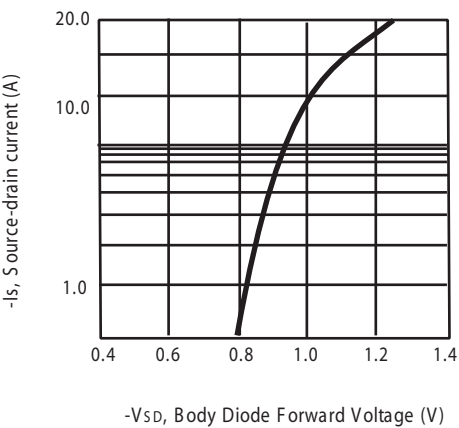
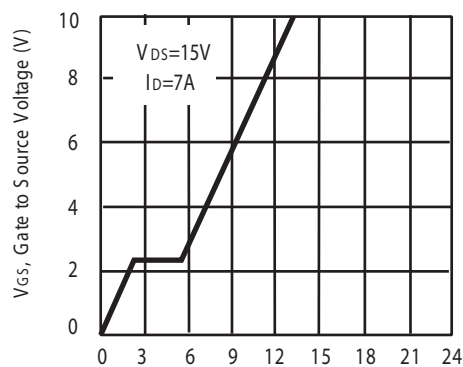


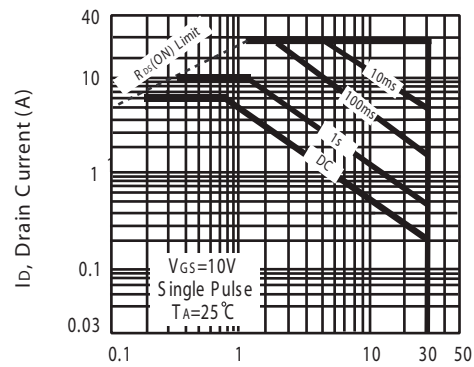
Figure 8. Body Diode Forward Voltage Variation with Source Current

STM8301

N-Channel

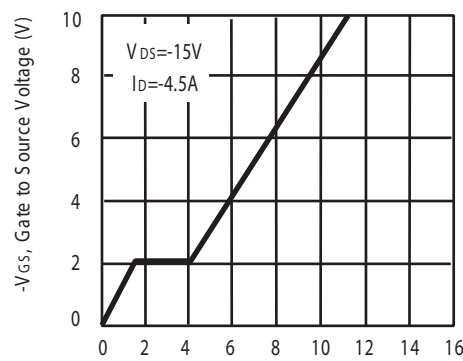


Q_g , Total Gate Charge (nC)
Figure 9. Gate Charge

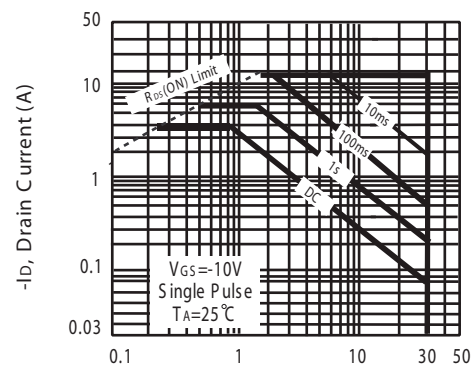


V_{DS} , Drain-Source Voltage (V)
Figure 10. Maximum Safe Operating Area

P-Channel



Q_g , Total Gate Charge (nC)
Figure 9. Gate Charge



$-V_{DS}$, Body Diode Forward Voltage (V)
Figure 10. Maximum Safe Operating Area

STM8301

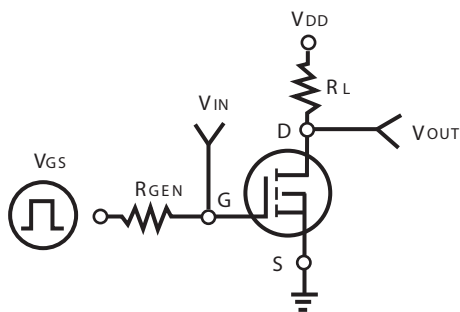


Figure 11. S switching Test Circuit

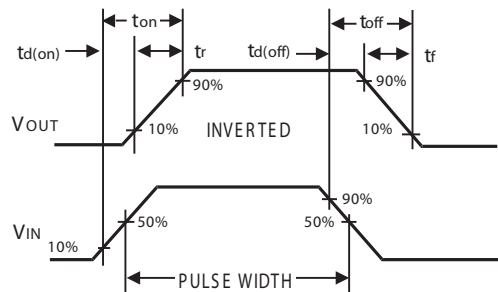
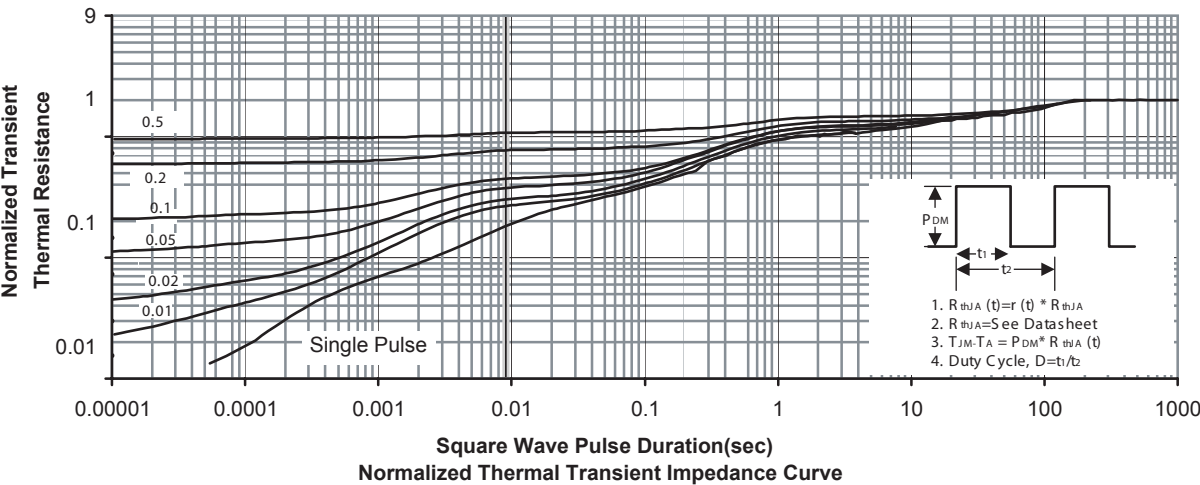
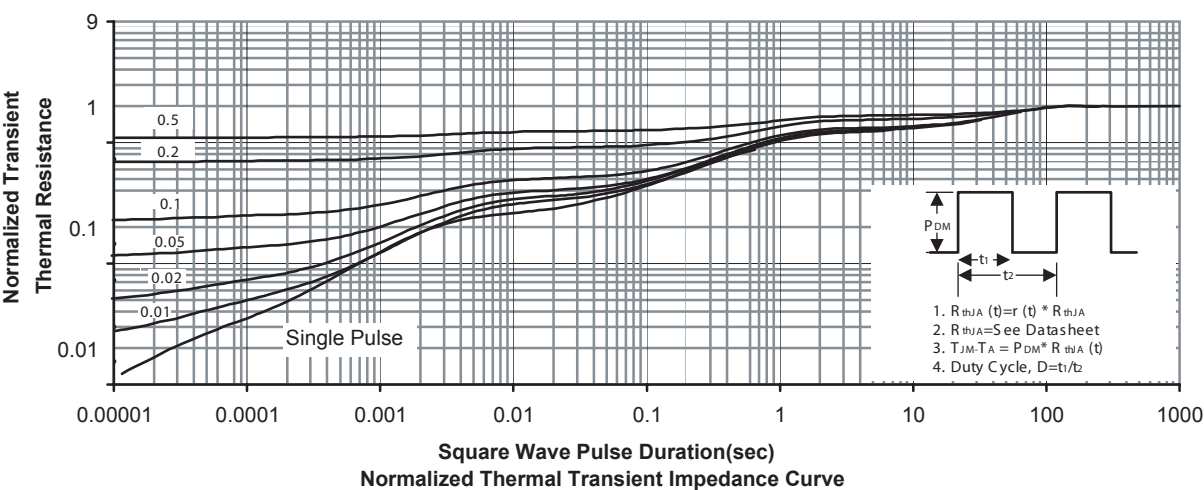


Figure 12. Switching Waveforms

N-Channel



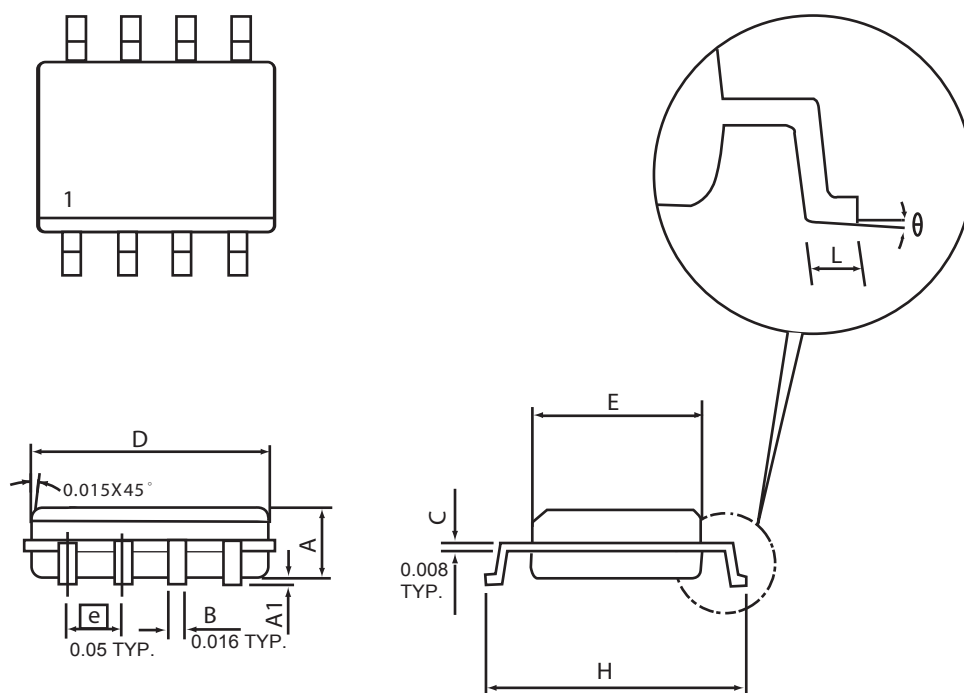
P-Channel



STM8301

PACKAGE OUTLINE DIMENSIONS

SO-8

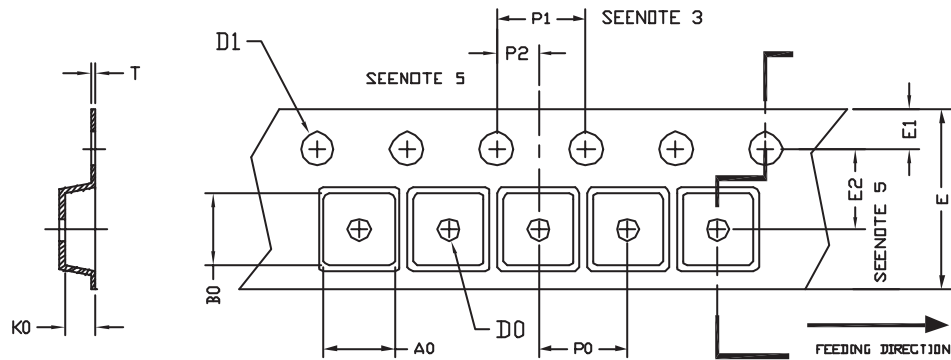


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
θ	0°	8°	0°	8°

STM8301

SO-8 Tape and Reel Data

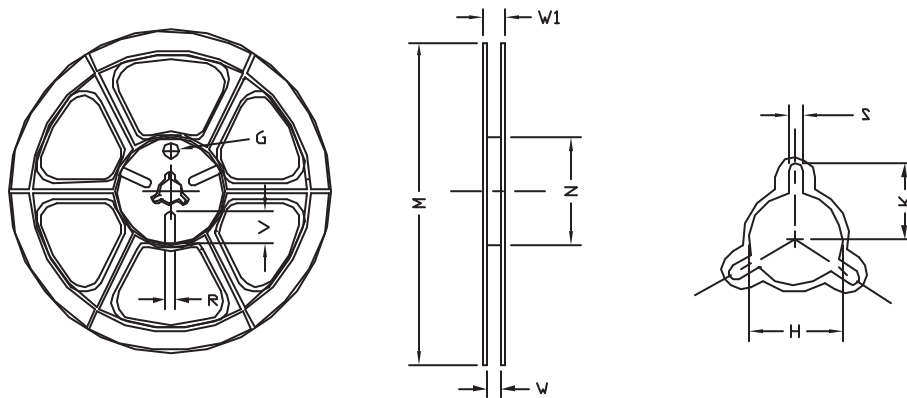
SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.40	5.20	2.10	$\phi 1.5$ (MIN)	$\phi 1.5$ + 0.1 - 0.0	12.0 ± 0.3	1.75	5.5 ± 0.05	8.0	4.0	2.0 ± 0.05	0.3 ± 0.05

SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330 ± 1	62 ± 1.5	12.4 + 0.2	16.8 - 0.4	$\phi 12.75$ + 0.15	---	2.0 ± 0.15	---	---	---